

# **Device Modeling Report**

COMPONENTS:

DIODE/ GENERAL PURPOSE RECTIFIER / PROFESSIONAL

PART NUMBER: 1SR159-200

MANUFACTURER: ROHM

REMARK: TC=25C

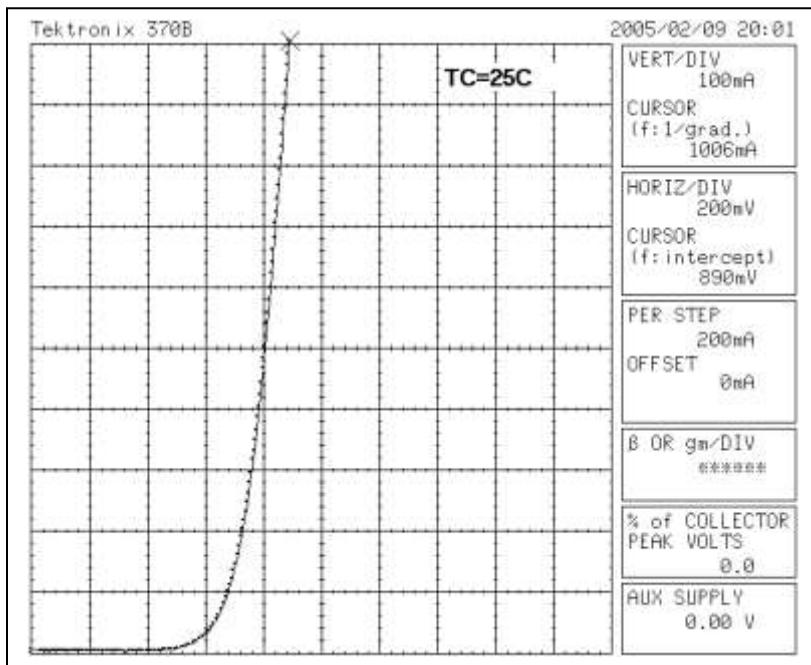


**Bee Technologies Inc.**

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

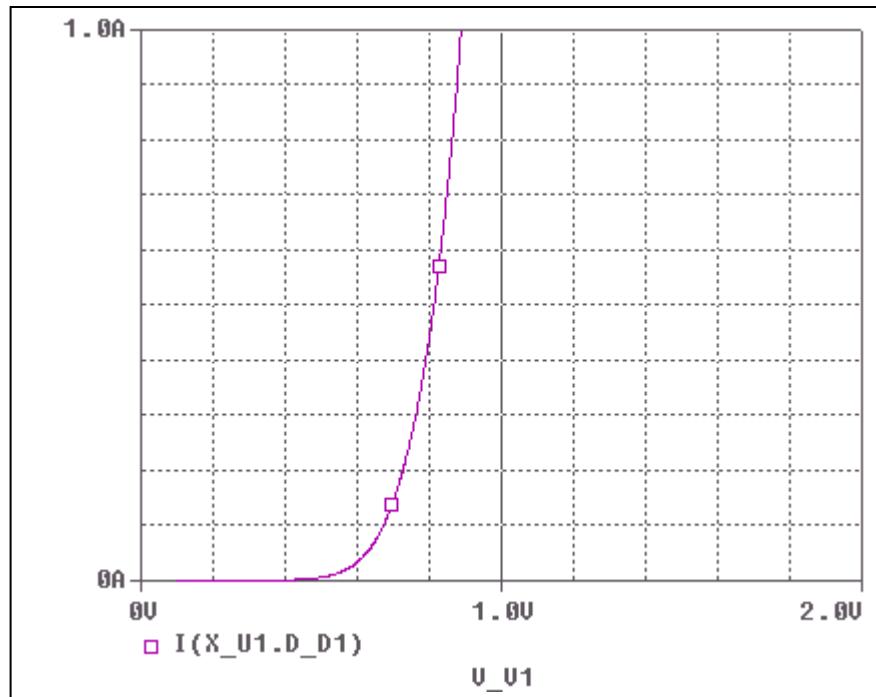
## Forward Current Characteristic

## Reference

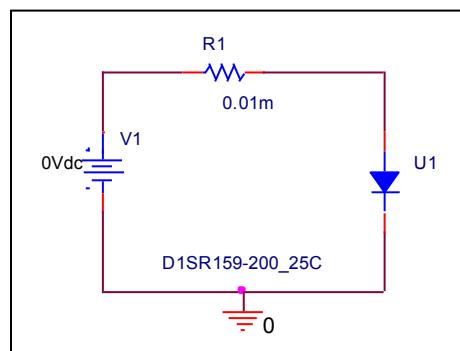


## Forward Current Characteristic

### Circuit Simulation Result

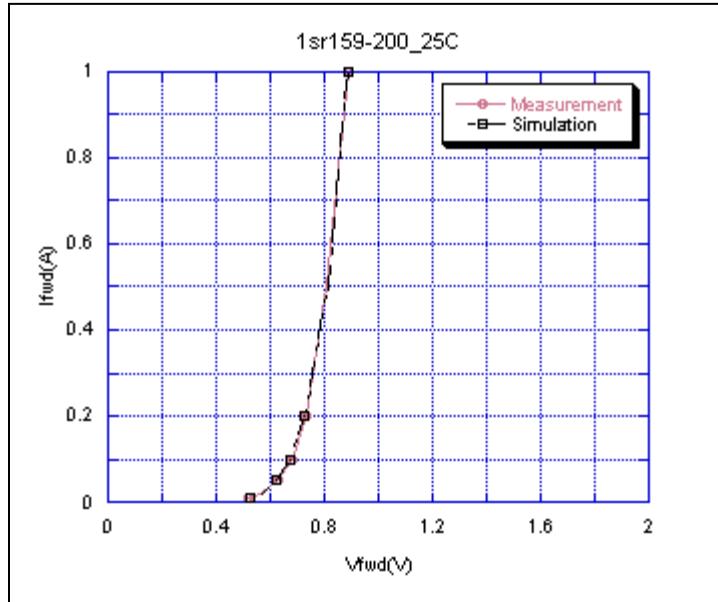


### Evaluation Circuit



## Comparison Graph

Circuit Simulation Result

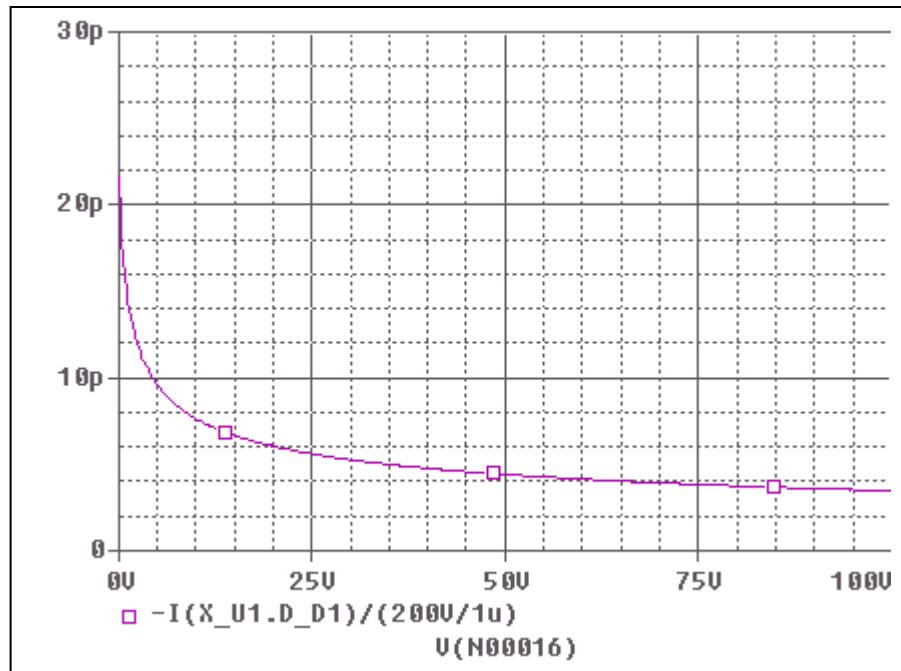


Simulation Result

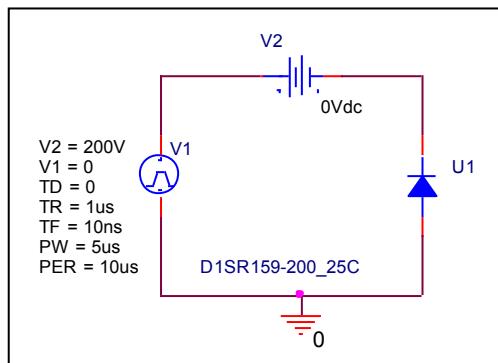
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.01	0.520	0.527	-1.35
0.02	0.566	0.568	-0.35
0.05	0.628	0.625	0.48
0.1	0.678	0.672	0.88
0.2	0.730	0.724	0.82
0.5	0.806	0.812	-0.74
1	0.890	0.888	0.22

## Capacitance Characteristic

### Circuit Simulation Result

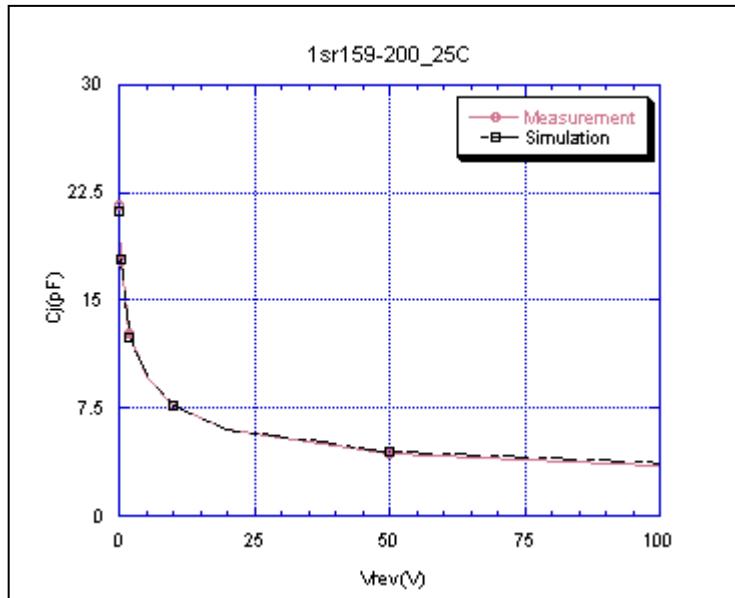


### Evaluation Circuit



## Comparison Graph

Circuit Simulation Result

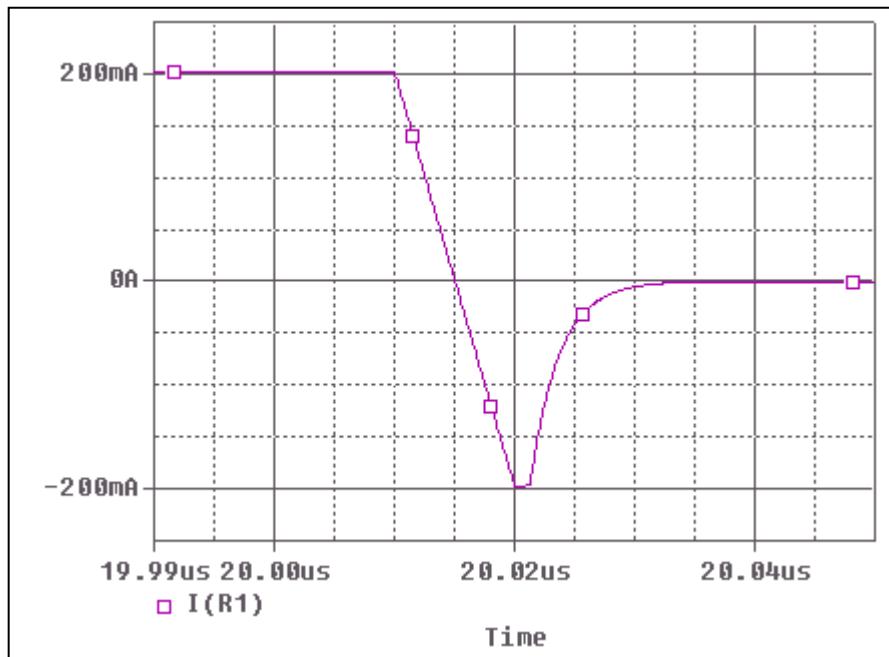


Simulation Result

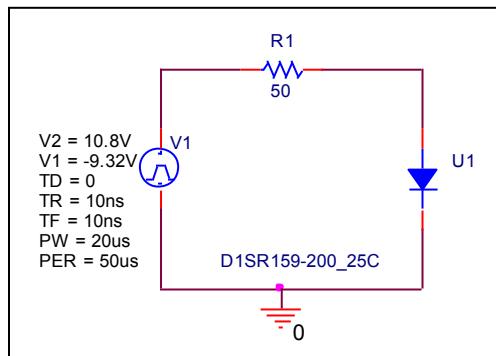
$V_{rev}$ (V)	$C_j$ (pF) Measurement	$C_j$ (pF) Simulation	%Error
0	23.185	23.185	0.00
0.1	21.588	21.146	2.05
0.2	20.365	20.350	0.07
0.5	17.681	17.782	-0.57
1	15.275	15.287	-0.08
2	12.705	12.374	2.61
5	9.674	9.607	0.69
10	7.672	7.651	0.27
20	6.033	6.038	-0.08
50	4.362	4.412	-1.15
100	3.428	3.462	-0.99

## Reverse Recovery Characteristic

### Circuit Simulation Result



### Evaluation Circuit

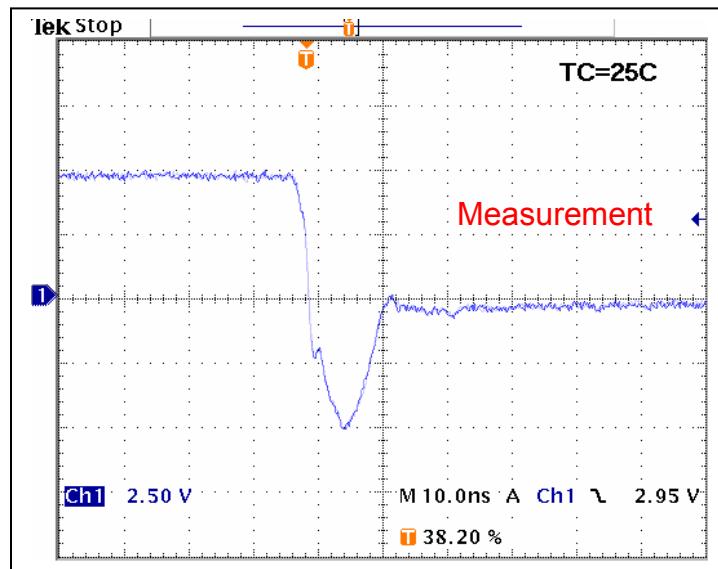


### Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trj	5.80	ns	5.78	ns	0.34
trb	5.40	ns	5.42	ns	0.37

## Reverse Recovery Characteristic

Reference



Trj = 5.80(ns)

Trb=5.40(ns)

Conditions: Ifwd=Irev=0.2(A), RI=50

